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REMARKS

Please change paragraph 3 of the Remarks as follows.

Specifically, as can be seen from the foregoing amendments, independent claim 1 has been

amended to recite a method of manufacturing an electronic device comprising the steps of (a) forming

on an underlying layer an insulating film made from one of an oxide film, a nitride film, an oxide

nitride film, an organic film and an organic-inorganic hybrid film; (b) forming a resist pattern on the

insulating film; (c) forming an insulating film pattern by etching the insulating film with the resist

pattern used as a mask; (d) conducting a plasma treatment on exposed portions of the underlying layer

and the insulating film pattern without removing the resist pattern after step (c) and (e) forming a

pattern for the underlying layer by etching the underlying layer with the resist pattern and the insulating

film pattern used as a mask after step (d). That is, in accordance with the present invention, since the

plasma treatment is conducted on exposed portions of the underlying layer and the insulating film

pattern without removing the resist pattern in step (d), etching-foreign-matters-generated in small

depositions generated on the insulating film or underlying layer when forming the insulating film

pattern the step (c) can be removed. Thereafter, since the pattern for the underlying layer is formed by

etching the underlying layer with the resist pattern and the insulating film pattern used as a mask, the

underlying layer pattern can be formed without being affected by the etching foreign matters and hence,

with no pattern defect such as an increase in the size of pattern damage.

Respectfully submitted,

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